L Number	Hits	Search Text	DB	Time stamp
1	32919	semiconductor with (light near3 emitt$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:27
2	6926	laser near3 chip$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:28
3	1224	(semiconductor with (light near3 emitt$3)) & (laser near3 chip$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:30
4	15	((semiconductor with (light near3 emitt$3)) & (laser near3 chip$3)) & (mount near3 member)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:33
5	4	(((semiconductor with (light near3 emitt$3)) & (laser near3 chip$3)) & (mount near3 member)) & high$3 & (thermal near3 expansion near3 coefficient)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:43
6	88	((semiconductor with (light near3 emitt$3)) & (laser near3 chip$3)) & high$3 & (thermal near3 expansion near3 coefficient)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:41
7	16	(((semiconductor with (light near3 emitt$3)) & (laser near3 chip$3)) & high$3 & (thermal near3 expansion near3 coefficient)) & ((layer$3 with stack$3) same surfac$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:47
8	16	((((semiconductor with (light near3 emitt$3)) & (laser near3 chip$3)) & high$3 & (thermal near3 expansion near3 coefficient)) & ((layer$3 with stack$3) same surfac$3)) & substrat$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:57
10	15	(((((semiconductor with (light near3 emitt$3)) & (laser near3 chip$3)) & high$3 & (thermal near3 expansion near3 coefficient)) & ((layer$3 with stack$3) same surfac$3)) & substrat$3) & nitrid$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:59